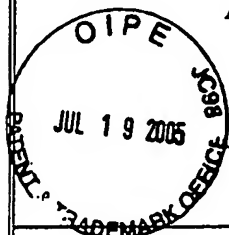


# INFORMATION DISCLOSURE CITATION IN AN APPLICATION



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 APPLICANT  
**Hideto HIDAHA**

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## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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						Yes	No
<i>ap</i>	A2	EP 1 225 591	07/24/2002	Kabushiki Kaisha Toshiba			
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<i>ap</i>	A1	DE 102 28 578 w/English abstract	01/16/2003	Mitsubishi Electric Corp.			

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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DATE CONSIDERED

*8/31/05*

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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## U.S. PATENT DOCUMENTS

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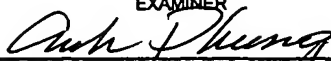
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						Yes	No

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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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